

## AMENDMENTS

This section presents changes to the specification and the claims in a clean-unmarked format. A version with markings to show the changes made by the current amendment is provided after the remarks section.

### **In The Specification:**

Please replace the paragraph beginning at page 14, line 6 with the paragraph:

B<sup>1</sup>

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Fig. 17 is a schematic cross-section showing a patterned masking layer 406 over a first dielectric material 404, which, in turn, is disposed over a substrate 402. In the illustrative embodiment, substrate 402 is a wafer with various electrical components, interconnections, and insulating regions formed therein. First dielectric 404 is any suitable material with a dielectric constant greater than or equal to the dielectric constant of silicon dioxide. Barium strontium titanate (BST) is one example of a high-k material.

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